

12-59 Air is blown over an aluminum plate mounted on an array of power transistors. The number of transistors that can be placed on this plate is to be determined.

Assumptions 1 Steady operating conditions exist. 2 The critical Reynolds number is $Re_{cr} = 5 \times 10^5$. 3 Radiation effects are negligible 4 Heat transfer from the back side of the plate is negligible. 5 Air is an ideal gas with constant properties. 6 The local atmospheric pressure is 1 atm.

Properties The properties of air at the film temperature of $(T_s + T_\infty)/2 = (65 + 35)/2 = 50^\circ\text{C}$ are (Table A-22)

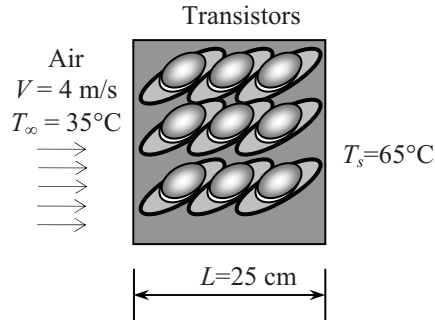
$$k = 0.02735 \text{ W/m}\cdot^\circ\text{C}$$

$$\nu = 1.798 \times 10^{-5} \text{ m}^2/\text{s}$$

$$Pr = 0.7228$$

Analysis The Reynolds number is

$$Re_L = \frac{VL}{\nu} = \frac{(4 \text{ m/s})(0.25 \text{ m})}{1.798 \times 10^{-5} \text{ m}^2/\text{s}} = 55,617$$



which is less than the critical Reynolds number. Thus the flow is laminar. Using the proper relation in laminar flow for Nusselt number, heat transfer coefficient and the heat transfer rate are determined to be

$$Nu = \frac{hL}{k} = 0.664 Re_L^{0.5} Pr^{1/3} = 0.664(55,617)^{0.5} (0.7228)^{1/3} = 140.5$$

$$h = \frac{k}{L} Nu = \frac{0.02735 \text{ W/m}\cdot^\circ\text{C}}{0.25 \text{ m}} (140.5) = 15.37 \text{ W/m}^2\cdot^\circ\text{C}$$

$$A_s = wL = (0.25 \text{ m})(0.25 \text{ m}) = 0.0625 \text{ m}^2$$

$$\dot{Q}_{conv} = hA_s(T_\infty - T_s) = (15.37 \text{ W/m}^2\cdot^\circ\text{C})(0.0625 \text{ m}^2)(65 - 35)^\circ\text{C} = 28.83 \text{ W}$$

Considering that each transistor dissipates 6 W of power, the number of transistors that can be placed on this plate becomes

$$n = \frac{28.8 \text{ W}}{6 \text{ W}} = 4.8 \longrightarrow \mathbf{4}$$

This result is conservative since the transistors will cause the flow to be turbulent, and the rate of heat transfer to be higher.